

<b>INFORMATION DISCLOSURE CITATION</b> (USE SEVERAL SHEETS IF NECESSARY)				<b>Complete if Known</b>	
				Application Number	10/553,573
				Filing Date	October 17, 2005
				First Named Inventor	Christian DUSSARRAT
				Art Unit	1715
Examiner Name	Elizabeth A. Burkhart				
Sheet	1	of	1	Attorney Docket Number	Serie 6070
<b>U.S. PATENT DOCUMENTS</b>					
Examiner Initials	Cite No.	Document Number	Publication Date	Name	Pages Column, Lines Where Relevant Passages or Relevant Figures Appear
	A1	US 5 932 286	8/03/1999	BEINGGLASS et al.	
<b>FOREIGN PATENT DOCUMENTS</b>					
Examiner Initials	Cite No.	Document Number	Publication Date	Name	Pages Column, Lines Where Relevant Passages or Relevant Figures Appear
<b>NON PATENT LITERATURE DOCUMENTS</b>					
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published			
	C1	PEREIRA, M.A. et al., "Silicon nitride deposited by ECR-CVD at room temperature for LOCOS isolation technology," Applied Surface Science 212-213 (2003), pp. 388-392			
	C2	YOTA, J. et al., "A comparative study on inductively-coupled plasma high-density plasma, plasma-enhanced, and low pressure chemical vapor deposition silicon nitride films," J. Vac. Sci. Technol. A 18(2), Mar/Apr 2000, pp. 372-376			
Examiner			Date Considered		
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